

M Zafar Iqbal

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/11202545/publications.pdf>

Version: 2024-02-01

31
papers

324
citations

1040056

9
h-index

888059

17
g-index

32
all docs

32
docs citations

32
times ranked

173
citing authors

#	ARTICLE	IF	CITATIONS
1	Simple method for direct synthesis of YBa ₂ Cu ₄ O ₈ at atmospheric oxygen pressure. Applied Physics Letters, 1993, 63, 257-259.	3.3	38
2	Ruthenium: A superior compensator of InP. Applied Physics Letters, 1998, 73, 3878-3880.	3.3	32
3	Characterization of deep levels introduced by alpha radiation in n-type silicon. Journal of Applied Physics, 1993, 73, 3698-3708.	2.5	30
4	Characterization of silver-related deep levels in silicon. Journal of Applied Physics, 1987, 62, 2853-2857.	2.5	28
5	Study of alpha radiation-induced deep levels in p-type silicon. Journal of Applied Physics, 1993, 73, 4240-4247.	2.5	27
6	Mechanism of decomposition of cuprous cyanide. Infrared and thermal evidence. Chemistry of Materials, 1993, 5, 1283-1286.	6.7	26
7	Role of the mid-gap level as the dominant recombination center in platinum doped silicon. Journal of Applied Physics, 1990, 67, 1130-1132.	2.5	24
8	Effect of ambient on photoluminescence from GaN grown by molecular-beam epitaxy. Journal of Electronic Materials, 2003, 32, 346-349.	2.2	20
9	Optical properties of a silver-related defect in silicon. Physical Review B, 2003, 67, .	3.2	15
10	Arsenic antisite defects in p-GaAs grown by metal-organic chemical-vapor deposition and the EL2 defect. Journal of Applied Physics, 2009, 106, .	2.5	9
11	Effects of annealing and γ irradiation on deep levels in silver-doped n-type silicon. Journal of Applied Physics, 1995, 77, 3315-3322.	2.5	8
12	Y-Ba-Cu (1-2-3) superconductor starting with copper cyanide. Journal of Materials Science Letters, 1991, 10, 1182-1183.	0.5	7
13	Study of the alpha irradiation and thermal annealing of gold-doped n-type silicon. Journal of Applied Physics, 1995, 77, 5572-5579.	2.5	7
14	Electrical characterization of alpha radiation-induced defects in p-GaAs grown by metal-organic chemical-vapor deposition. Journal of Applied Physics, 2007, 101, 063701.	2.5	7
15	Study of deep levels in alpha-irradiated silver-doped p-type silicon. Journal of Applied Physics, 1995, 77, 5050-5059.	2.5	6
16	Bleaching of the interstitial iron donor in silicon by transition metal impurities. Semiconductor Science and Technology, 1996, 11, L129-L132.	2.0	5
17	Characteristics of deep levels associated with rhodium impurity in n-type GaAs. Journal of Applied Physics, 2003, 94, 3115-3120.	2.5	5
18	Interaction of iron with transition metals and alpha radiation in thermally quenched p-silicon. Semiconductor Science and Technology, 1997, 12, 1100-1105.	2.0	4

#	ARTICLE	IF	CITATIONS
19	Î±-radiation induced deep levels in low-doped n-type silicon. Journal of Applied Physics, 1990, 68, 887-889.	2.5	3
20	Deep levels in alpha-irradiated platinum doped n-type silicon. Journal of Applied Physics, 1994, 76, 2553-2555.	2.5	3
21	Interaction of Î±-radiation induced defects with Pd-related deep levels in silicon. Journal of Applied Physics, 1994, 75, 7737-7744.	2.5	3
22	Rhodium-related deep levels in n-type MOCVD GaAs. Physica B: Condensed Matter, 2001, 308-310, 816-819.	2.7	3
23	4d transition-metal impurity rhodium in GaAs grown by metal-organic chemical vapor deposition. Journal of Applied Physics, 2008, 104, 113708.	2.5	3
24	0.75 eV killer centre? in red-emitting GaP LEDs. Applied Physics A: Solids and Surfaces, 1983, 32, 223-224.	1.4	2
25	Electron capture cross sections of the platinum donor level in silicon. Semiconductor Science and Technology, 1990, 5, 1133-1135.	2.0	2
26	Osmium Related Deep Levels in Indium Phosphide. Physica Status Solidi A, 1999, 171, 521-537.	1.7	2
27	Role of boat material in the synthesis of 123 superconductor from copper cyanide. Journal of Materials Science Letters, 1993, 12, 607-608.	0.5	2
28	Atmospheric-pressure synthesis of the YBa ₂ Cu ₄ O ₈ superconductor using Cu ₂ (CN) ₂ . Superconductor Science and Technology, 1994, 7, 563-568.	3.5	1
29	Osmium impurity-related deep levels in n-type GaAs. Journal of Applied Physics, 2005, 98, 083709.	2.5	1
30	Osmium related deep levels in n-type GaAs. Physica B: Condensed Matter, 2003, 340-342, 358-361.	2.7	0
31	Effects of irradiation and annealing on deep levels in rhodium-doped p-GaAs grown by metal-organic chemical-vapor deposition. Journal of Applied Physics, 2011, 109, 113705.	2.5	0